# P-Channel 30-V (D-S) MOSFET

### **Key Features:**

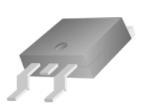
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

## **Typical Applications:**

- Load Switches
- DC/DC Conversion
- Motor Drives

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
-30	$10.5 @ V_{GS} = 10V$	-56		
	16 @ V <sub>GS</sub> = 4.5V	-46		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Limit	Units		
Drain-Source Voltage		$V_{DS}$	-30	V		
Gate-Source Voltage		$V_{GS}$	±20	V		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> =25°C	$I_D$	-56	Α		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-200	ζ		
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	-50	Α			
Power Dissipation <sup>a</sup>	T <sub>C</sub> =25°C	$P_{D}$	50	W		
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	$R_{\theta JA}$	40	°C/W		
Maximum Junction-to-Case	$R_{\theta JC}$	3	C/VV		

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#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

#### **Electrical Characteristics**

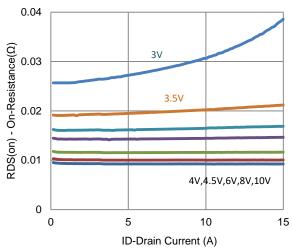
Parameter	Symbol	mbol Test Conditions		Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valta da Brain Currant	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, V_{GS} = 10 \text{ V}$	-80			Α	
Dania Commo On Bosistano a	r	$V_{GS} = -10 \text{ V}, I_{D} = -20 \text{ A}$			10.5	mΩ	
Drain-Source On-Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_{D} = -16 \text{ A}$			16	11177	
Forward Transconductance a	g <sub>fs</sub>	$V_{DS} = -15 \text{ V}, I_{D} = -20 \text{ A}$		33		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{S} = -25 \text{ A}, V_{GS} = 0 \text{ V}$		-0.94		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V},$		28			
Gate-Source Charge	$Q_gs$	$I_{DS} = -13 \text{ V}, \text{ V}_{GS} = -4.3 \text{ V},$ $I_{D} = -20 \text{ A}$		11		nC	
Gate-Drain Charge	$Q_gd$	10 = 20 A		8.5			
Turn-On Delay Time	t <sub>d(on)</sub>	$V_{DS} = -15 \text{ V}, R_1 = 0.75 \Omega,$		6			
Rise Time	t <sub>r</sub>	$V_{DS} = -15 \text{ V}, \text{ K}_{L} = 0.75 \Omega,$ $I_{D} = -20 \text{ A},$		8		nc	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		91		ns	
Fall Time	t <sub>f</sub>	V GEN = 10 V, 1 (GEN = 0 12		35			
Input Capacitance	C <sub>iss</sub>			2308			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		282		pF	
Reverse Transfer Capacitance	$C_{rss}$			230			

#### Notes

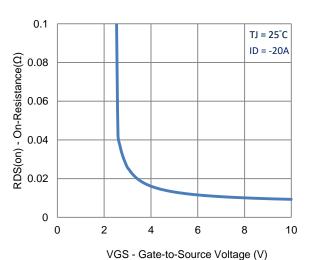
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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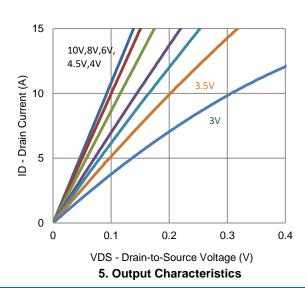
### **Typical Electrical Characteristics**



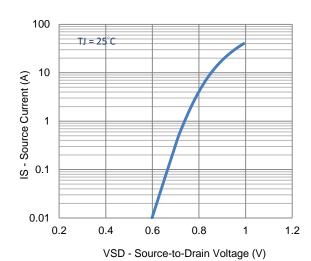
#### 1. On-Resistance vs. Drain Current



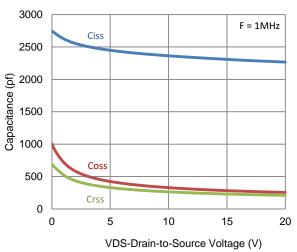
3. On-Resistance vs. Gate-to-Source Voltage



2. Transfer Characteristics

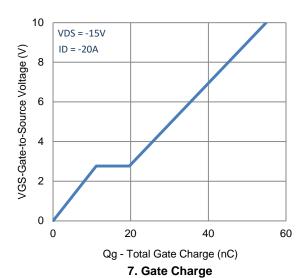


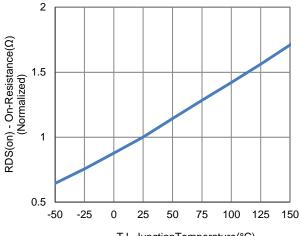
4. Drain-to-Source Forward Voltage



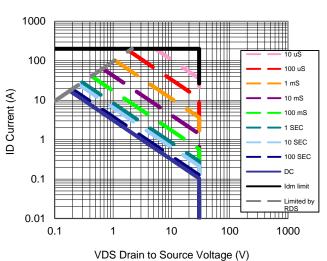
6. Capacitance

### **Typical Electrical Characteristics**

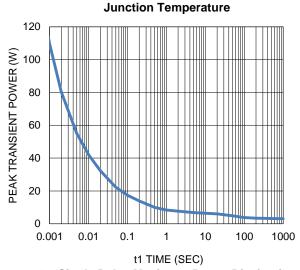




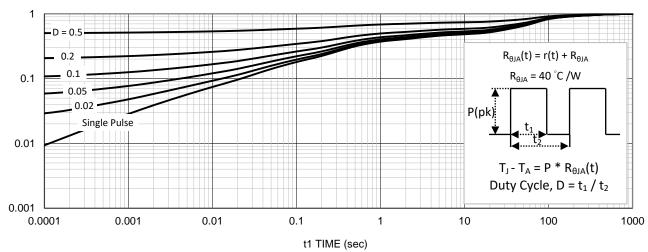
TJ -JunctionTemperature(°C)
8. Normalized On-Resistance Vs



9. Safe Operating Area

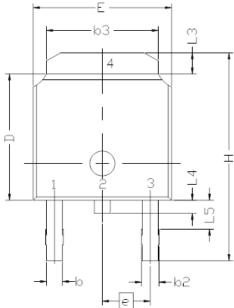


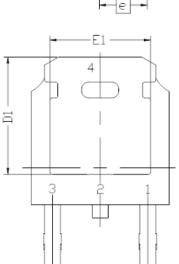
10. Single Pulse Maximum Power Dissipation



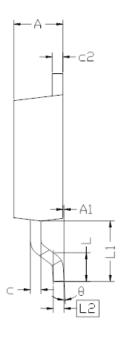
11. Normalized Thermal Transient Junction to Ambient

### **Package Information**





SINGLE ROWNEW



	DIMENS:	[DNAL F	REQMTS
SYMBOL	MIN	NDM	MAX
E	6.40	6.60	6.731
L	1.40	1.52	1.77
L1		.743 RI	
L2		.508 BS	
L3	0.89		1.27
L4	0.64		1.01
L5			
D	6.00	6.10	6,223
Н	9.40	10.00	10.40
b	0.64	0.76	0,88
b2	0.77	0.84	1.14
b3	5.21	5.34	5.46
е	2.	286 BS	SC.
Α	2.20	2.30	2,38
A1	0		0.127
C	0.45	0.50	0.60
c2	0.45	0.50	0.58
D1	5,30		
E1	4.40		
θ	0°		10°

#### Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.